

## **Quarterly Reliability Monitoring Results**

## Quarters: Q1/2022 to Q4/2023

Based on structural similarity

Supplier Nexperia B.V. Name of Laboratory Assembly reliability labs		User Part Number BC857BQC Part Description											
									Nexperia DHAM Small Signal Bipolar Transistor				
									MCD package				
		Test		Test Conditions	Duration	# Lots	# Quantity	# Rejects					
			TEST										
	Pre- and Post-Stress												
# 1	Electrical Test	Tamb = 25 °C	N/A	see below	all parts	see below							
l		JESD22-A113											
	PC	Bake Tamb = 125 °C Soak Tamb = 85 °C, RH = 85%	24 hours 168 hours										
# 2	Preconditioning	Reflow soldering	3 cycles	464	20960	0							
# Z		MIL-STD-750-1	,	704	20300								
	HTRB	M1039 Method A											
		Tj = Tjmax, Vr = 100% of max. datasheet											
# 5	Bias	reverse voltage	1000 hours	415	18680	0							
	TC	JESD22-A104				_							
# 7	Temperature Cycling	-65 °C to Tjmax, not to exceed 150°C	500 cycles	116	5240	0							
	UHAST	JESD22-A118											
# 8 <b>or</b>	Unbiased HAST	Tamb = 130 °C, RH = 85 %	— 96 hours	116	5240	0							
		JESD22-A102											
	AC	Tamb = 121 °C, RH = 100 %											
# 8a	Autoclave	Pressure = 205 kPa (29.7 psia)											
	USTOD	JESD22-A101											
	<b>H3TRB</b> High Humidity High	Tamb = 85 °C, RH = 85%, VR = 80 % of											
# 9	Temperature Reverse Bias		1000 hours	116	5240	0							
" )		MIL-STD-750 Method 1037	1000 110015	110	3270	<u> </u>							
	IOL	ton = toff, devices powered to insure $\Delta T_j$ =											
# 10	Intermittent Operating Life		333 hours	116	5240	0							
	RSH	JESD22-A111											
# 20	Resistance to Solder Heat	260 °C ± 5 °C	10 s	n.a.	n.a.	n.a.							
# 21	<b>SD</b> Solderability	J-STD-002		86	2580	0							
# 41	Solderability	3 310 002		00	∠30U	U							

<sup>[1]</sup> The maximum applied voltage is limited by test chamber set up and does not exceed 115V.

## Calculation of FIT and MTTF

Test considered for FIT calculation: High Temperature Reverse Bias (HTRB, Test # 5) Confidence level 60%, derated to 55 °C, activation energy 0.7 eV, test time 168 to 1000 hours

Wafer Fab	Technology	Quantity	Rejects	Failure Rate (FIT)	MTTF (hrs)
Nexperia	Small Signal Bipolar				
DHAM	Transistor	18680	0	0,23	4,40E+09

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